

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	62031	"thin film transistor" or TFT	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 17:33
2	BRS	L2	868856	gate	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 17:33
3	BRS	L3	178467 5	substrate	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 17:33
4	BRS	L4	421191	impurity or impurities	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 17:33
5	BRS	L5	274141	implant\$6 or inplant\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 17:33

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6	BRS	L6	558585	diffus\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 17:33
7	BRS	L7	55932	asi or a-si or "amorphous silicon"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 17:33
8	BRS	L8	628490 9	resistance or R	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 17:33
9	BRS	L9	2285	(impurity or impurities) near4 (asi or a-si or "amorphous silicon")	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 17:33
10	BRS	L10	951	((impurity or impurities) near4 (asi or a-si or "amorphous silicon")) same gate	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 17:33

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11	BRS	L11	528	((impurity or impurities) near4 (asi or a-si or "amorphous silicon")) same gate) same substrate	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B	2004/06/17 17:34
12	BRS	L13	403	(asi or a-si or "amorphous silicon") near8 gate near8 (impurity or impurities)	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B	2004/06/17 17:34
13	BRS	L14	30	((asi or a-si or "amorphous silicon") near8 gate near8 (impurity or impurities)) near8 surface	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B	2004/06/17 17:34
14	BRS	L16	5829	(remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B	2004/06/17 17:34
15	BRS	L17	1471	((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")) same source same drain	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B	2004/06/17 17:34

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16	BRS	L18	979	((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")) same source same drain) same gate	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B	2004/06/17 17:35
17	BRS	L19	756	((((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")) same source same drain) same gate) and ("thin film transistor" or TFT)	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B	2004/06/17 17:35
18	BRS	L21	122	((((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")) same source same drain) same gate) same "channel region"	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B	2004/06/17 17:35
19	BRS	L23	968	((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")) near8 (contact or channel)	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B	2004/06/17 17:36
20	BRS	L25	5433802	diffus\$6 or dop\$6 or push\$6 or dispers\$6 or scatter\$6 or distribut\$6 or forc\$4 or emerg\$4	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B	2004/06/17 17:36

	Type	L #	Hits	Search Text	DBs	Tim Stamp
21	BRS	L26	13259	(diffus\$6 or dop\$6 or push\$6 or dispers\$6 or scatter\$6 or distribut\$6 or forc\$4 or emerg\$4) near4 (phosphorus or P or impurity or impurities) near8 contact	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B	2004/06/17 17:37
22	BRS	L27	577	((diffus\$6 or dop\$6 or push\$6 or dispers\$6 or scatter\$6 or distribut\$6 or forc\$4 or emerg\$4) near4 (phosphorus or P or impurity or impurities) near8 contact) same (asi or a-si or "amorphous silicon")	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B	2004/06/17 17:37
23	BRS	L12	73	(((impurity or impurities) near4 (asi or a-si or "amorphous silicon")) same gate) same substrate) same (implant\$6 or inplant\$6)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B	2004/06/17 17:38
24	BRS	L15	17	((asi or a-si or "amorphous silicon") near8 gate near8 (impurity or impurities)) near8 surface) and ("thin film transistor" or TFT)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B	2004/06/17 17:38
25	BRS	L20	540	(((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")) same source same drain) same gate) and ("thin film transistor" or TFT)) and (@ad<20010219)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B	2004/06/17 17:38

	Type	L #	Hits	Search Text	DBs	Tim Stamp
26	BRS	L22	104	(((((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")) same source same drain) same gate) same "channel region") and ("thin film transistor" or TFT)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B	2004/06/17 17:38
27	BRS	L24	21	((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")) near8 (contact or channel) near16 (resistance or R)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B	2004/06/17 17:38
28	BRS	L28	389	((diffus\$6 or dop\$6 or push\$6 or dispers\$6 or scatter\$6 or distribut\$6 or forc\$4 or emerg\$4) near4 (phosphorus or P or impurity or impurities) near8 contact) same (asi or a-si or "amorphous silicon") and ("thin film transistor" or TFT)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B	2004/06/17 17:38
29	BRS	L29	217	((((diffus\$6 or dop\$6 or push\$6 or dispers\$6 or scatter\$6 or distribut\$6 or forc\$4 or emerg\$4) near4 (phosphorus or P or impurity or impurities) near8 contact) same (asi or a-si or "amorphous silicon") and ("thin film transistor" or TFT)) and (@ad<20010219))	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B	2004/06/17 17:38
30	BRS	L30	32	diffus\$6 near4 (phosphorus or P or phosphorous) near4 "contact portion"	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B	2004/06/17 17:43

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31	BRS	L32	6303	(impurity or impurities or Phosphorous or P or phosphorus) near4 7	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 17:43
32	BRS	L33	67286	diffus\$6 near4 (phosphorus or P or phosphorous or impurity or impurities)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 17:43
33	BRS	L34	1140	32 and 33	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 17:43
34	BRS	L35	390	34 and 1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 18:07
35	BRS	L36	268	35 and (@ad<20010219)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/17 18:07